



40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C	
40V	4.5mΩ @ V _{GS} = 10V	95A	

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET has been designed to meet the stringent requirements of Automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

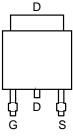
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ⁽²⁾
- Weight: 0.33 grams (Approximate)

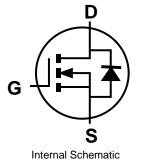




Top View



Top View Pin Out



Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH4005SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



H4005S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Digit of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	40	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 7)	$T_{C} = +25^{\circ}C$ (Note 10) $T_{C} = +100^{\circ}C$	I _D	95 73	А
Maximum Body Diode Forward Current (Note 7)	T _C = +25°C	Is	150	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	150	Α	
Avalanche Current, L=0.1mH		I _{AS}	32.5	Α
Avalanche Energy, L=0.1mH		E _{AS}	52.8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	$T_A = +25$ °C	P_D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	38	°C/W
Total Power Dissipation (Note 7)	$T_C = +25$ °C	P_D	100	W
Thermal Resistance, Junction to Case (Note 7)		R ₀ JC	1.5	°C/W
Operating and Storage Temperature Range		$T_{J_{i}}T_{STG}$	-55 to +175	°C

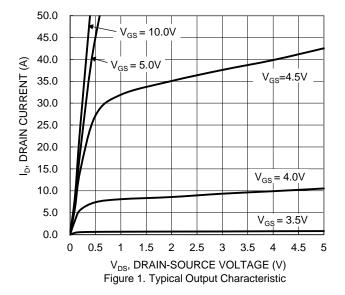
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		3.6	4.5	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	V_{SD}		0.9	_	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{ISS}	_	3,062	_		V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss		902.2	_	pF		
Reverse Transfer Capacitance	C _{RSS}		179.2	_			
Gate Resistance	R _G	_	0.67	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_G		49.1	_	V		
Gate-Source Charge	Q_{GS}	_	10.3	_	nC	$V_{DD} = 20V, I_D = 50A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q_{GD}	_	13	_			
Turn-On Delay Time	t _{D(ON)}	_	8.7	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{G} = 3\Omega$	
Turn-On Rise Time	t _R	_	6.8	_			
Turn-Off Delay Time	t _{D(OFF)}	_	18.6	_	ns		
Turn-Off Fall Time	t _F	_	7.3	_			
Body Diode Reverse Recovery Time	t _{RR}	_	31.8	_	ns	L E0A di/dt _ 100A/ug	
Body Diode Reverse Recovery Charge	Q _{RR}	_	26.5	_	nC	$I_F = 50A$, di/dt = 100A/ μ s	

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.
 10. Package limited.





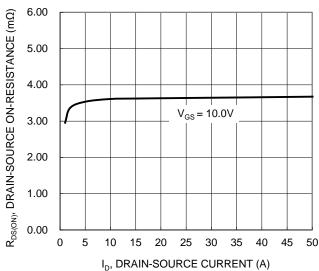


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

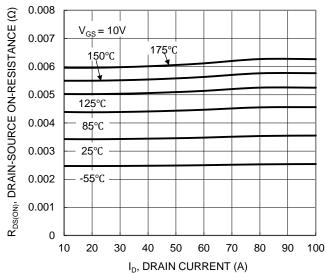
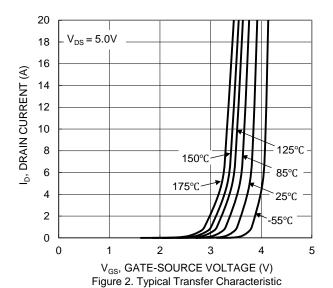
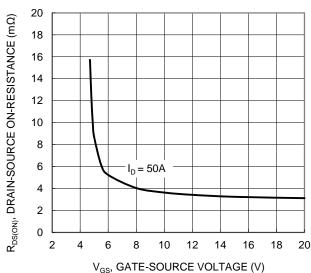


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





V_{GS}, GATE-SOURCE VOLTAGE (V)
Figure 4. Typical Transfer Characteristic

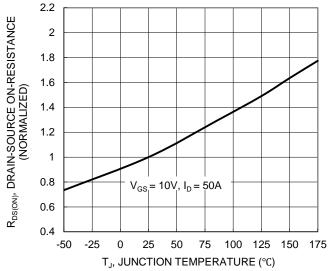


Figure 6. On-Resistance Variation with Temperature



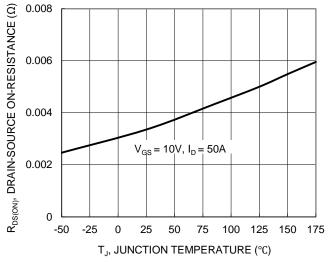
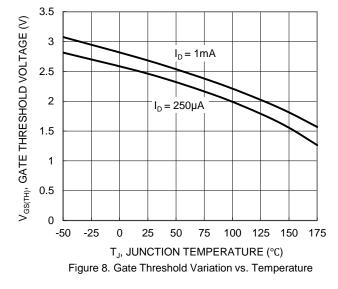


Figure 7. On-Resistance Variation with Temperature



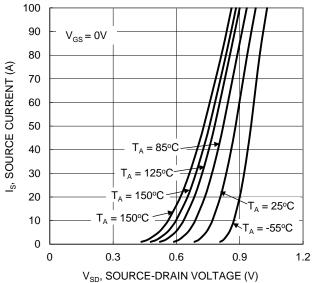
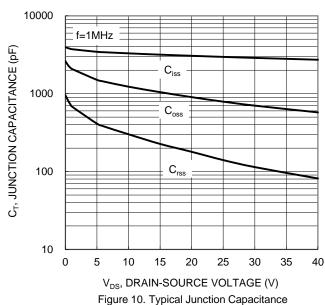


Figure 9. Diode Forward Voltage vs. Current



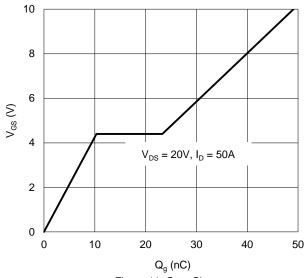


Figure 11. Gate Charge

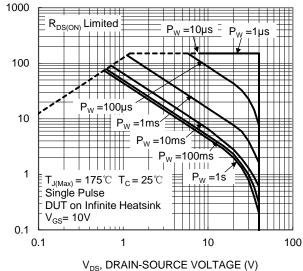


Figure 12. SOA, Safe Operation Area

ID, DRAIN CURRENT (A)



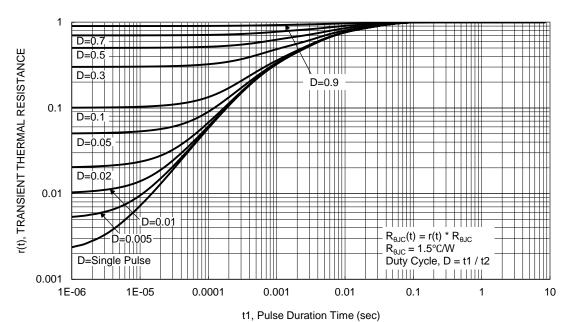


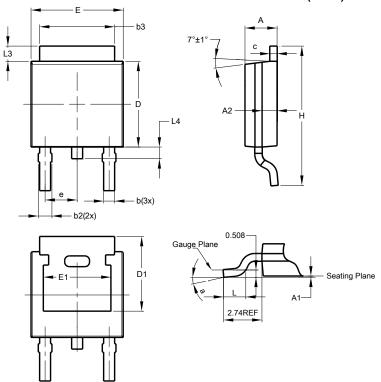
Figure 13. Transient Thermal Resistance



Package Outline

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

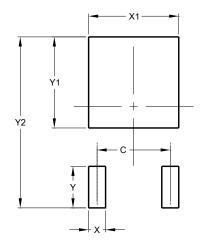


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
Г	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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